

Fig. 1C (After 'Conditioning')

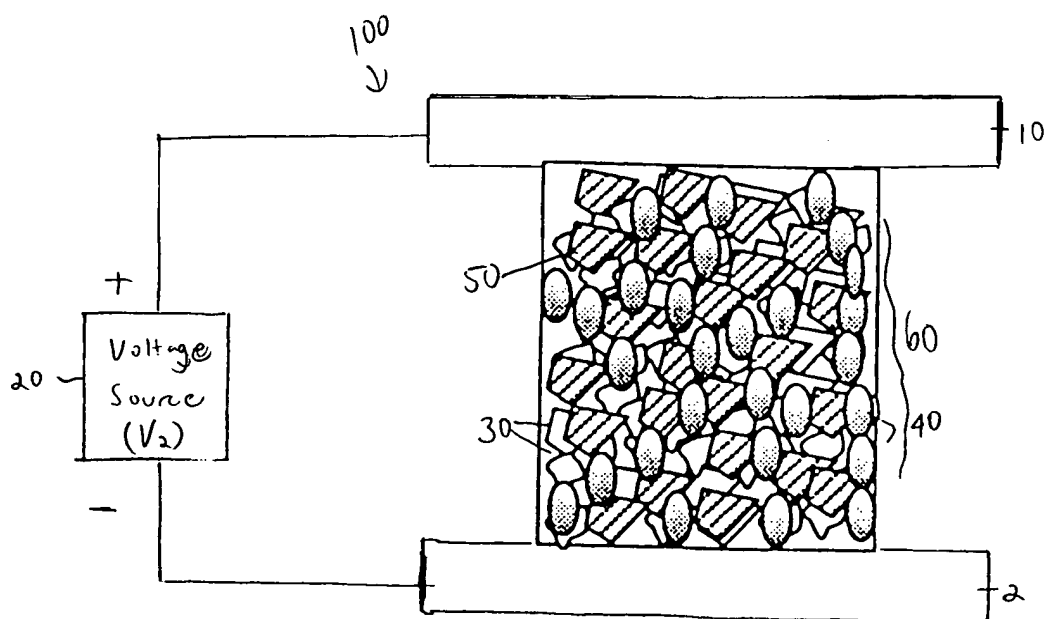


Fig. 1D (After 'Write')

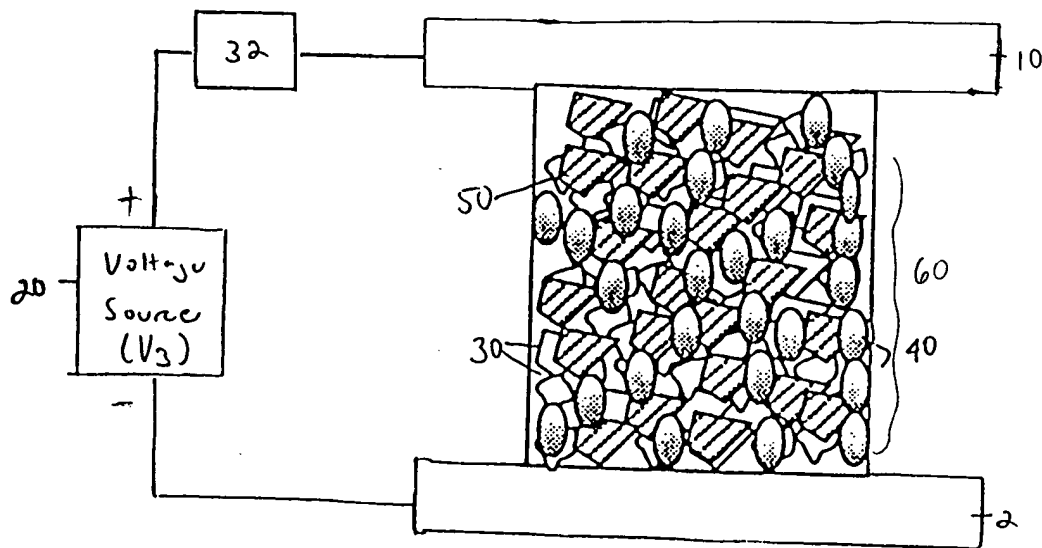


Fig. 1E (Read-out Voltage)

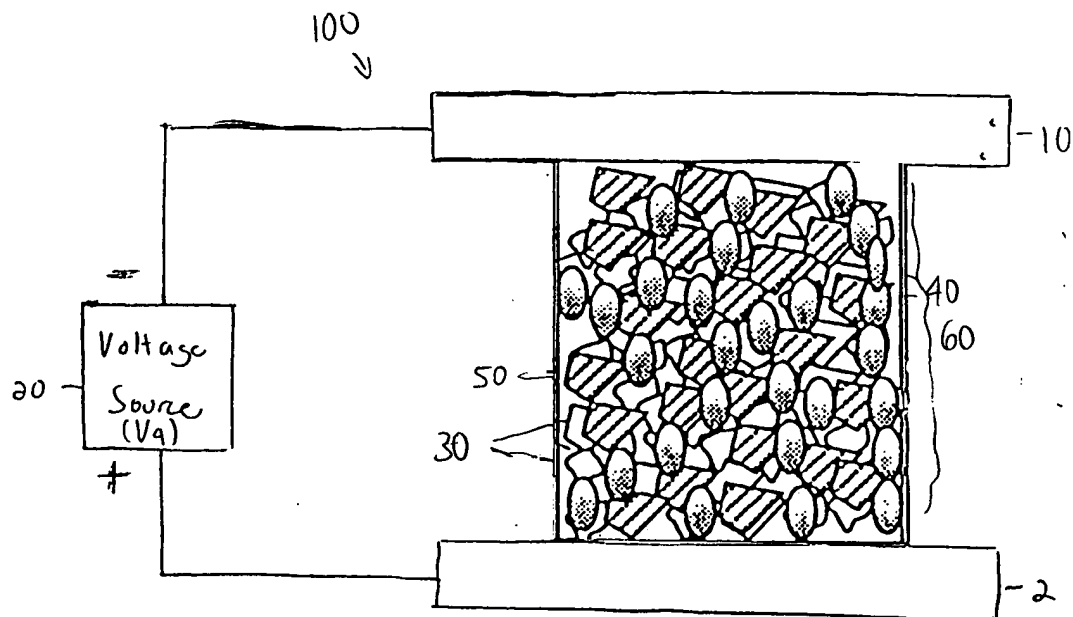


Fig. 1F (After 'Erase')

101  
↓

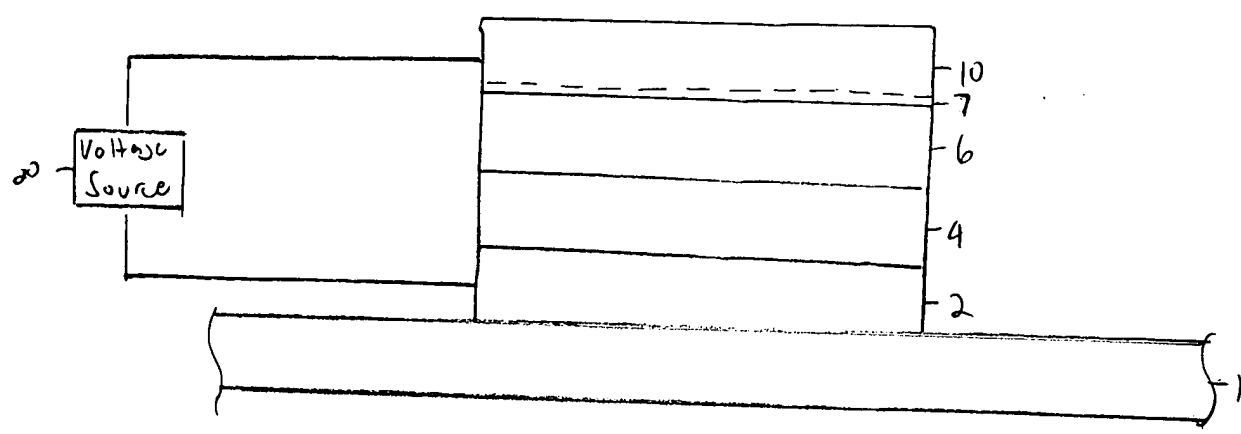


Fig. 2A

101  
↓

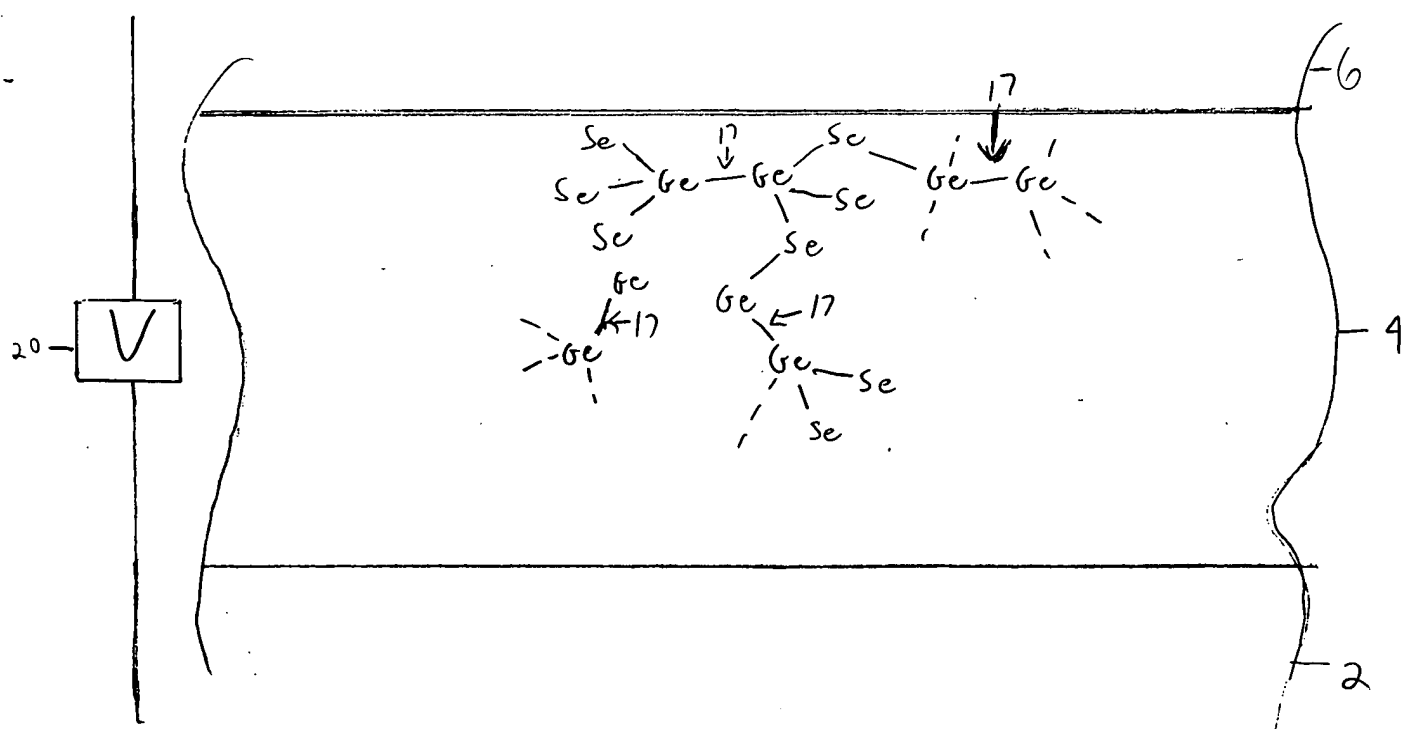
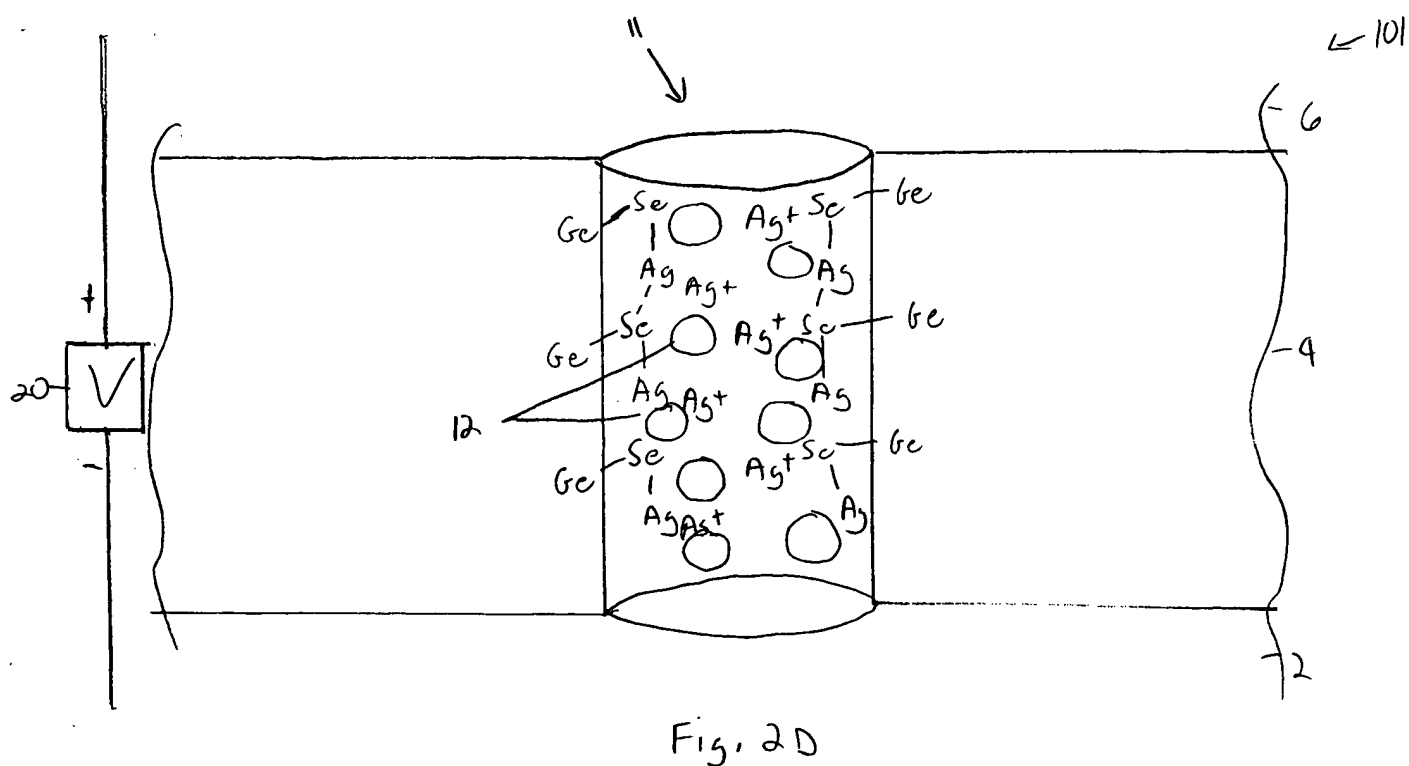
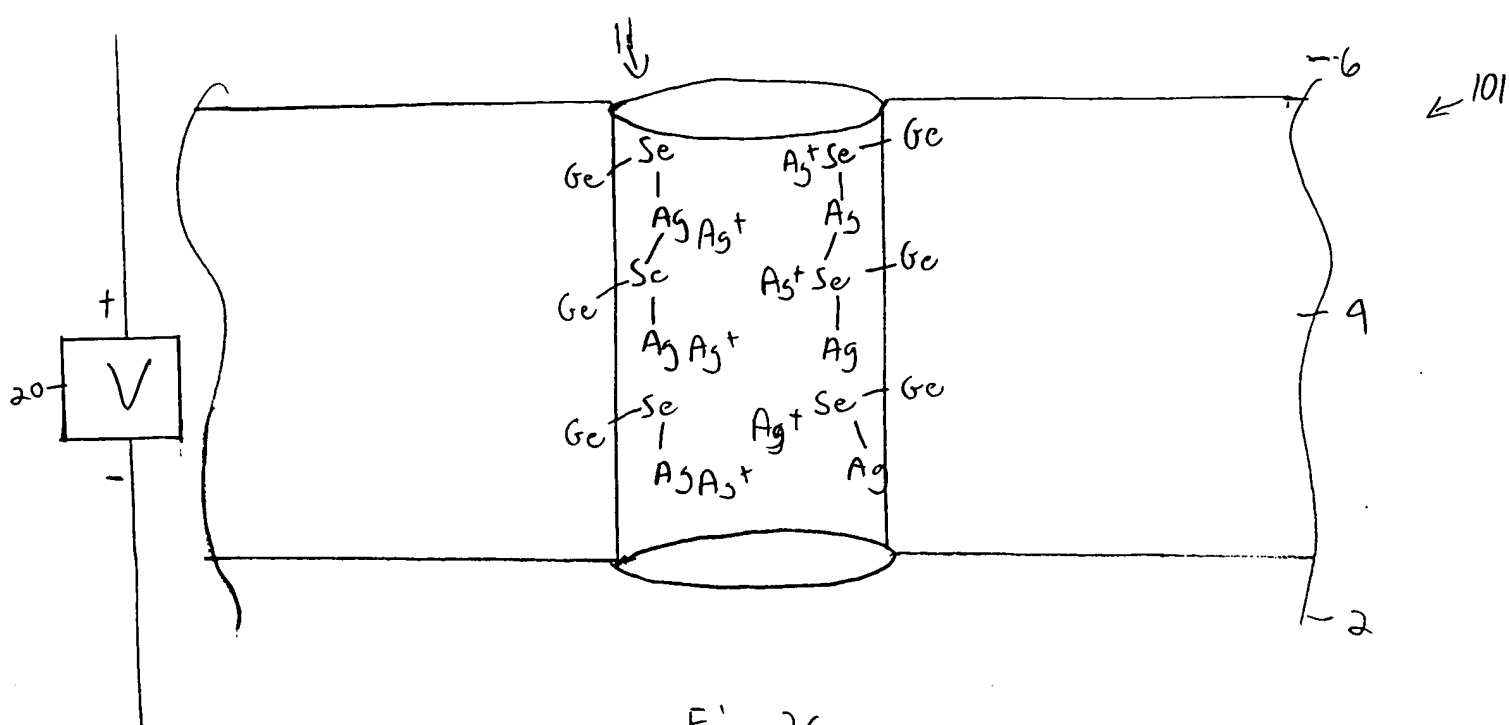


Fig. 2B



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App No.: Not Yet Assigned

Docket No.: M4065.0644/P644

Inventor: Kristy A. Campbell

Title: RESISTANCE VARIABLE MEMORY ELEMENTS BASED  
ON POLARIZED SILVER-SELENIDE NETWORK GROWTH

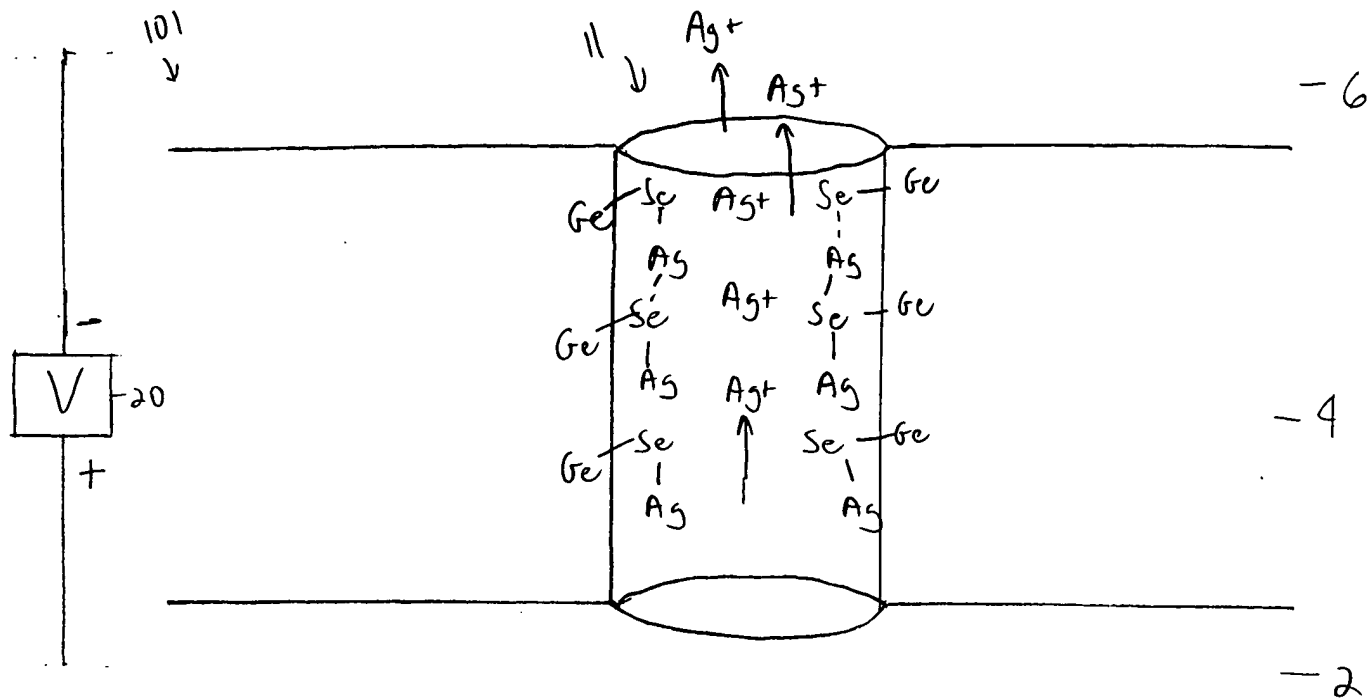


Fig. 2E

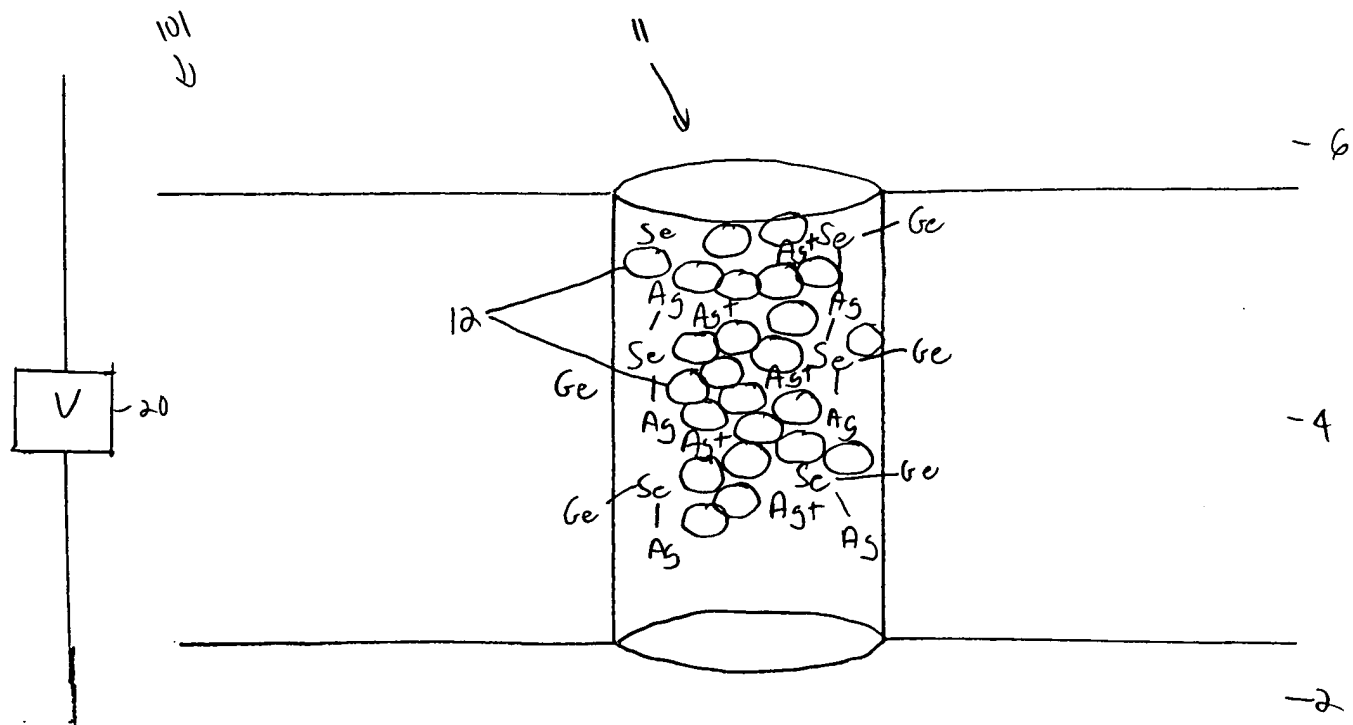


Fig. 2F

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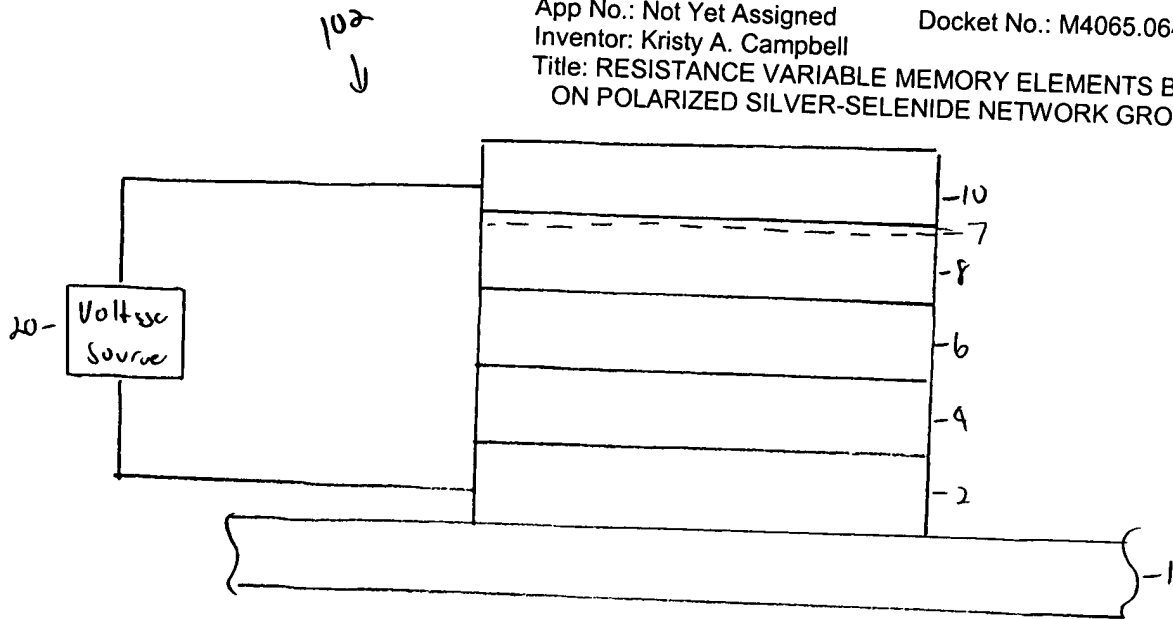


Fig. 3A

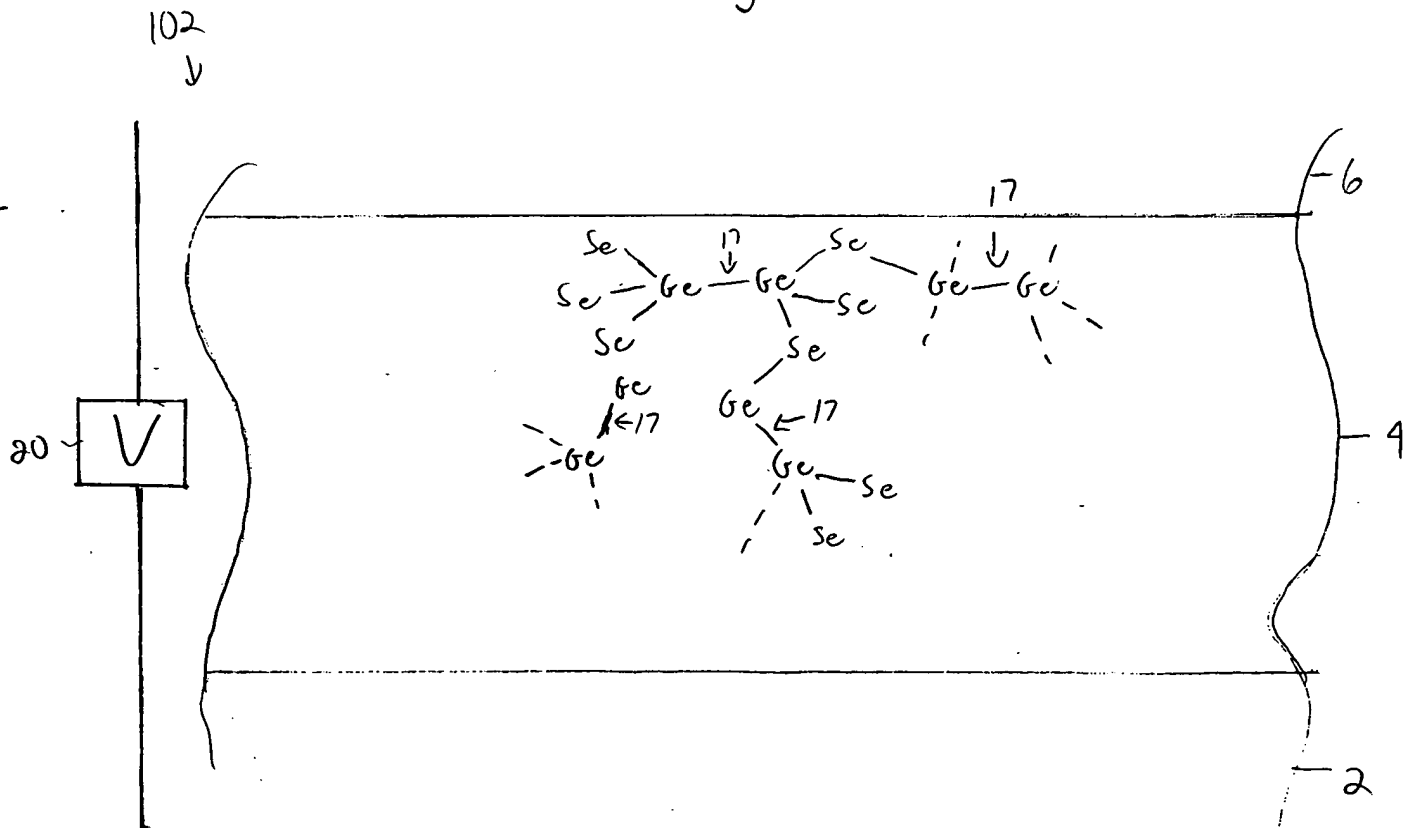


Fig. 3B

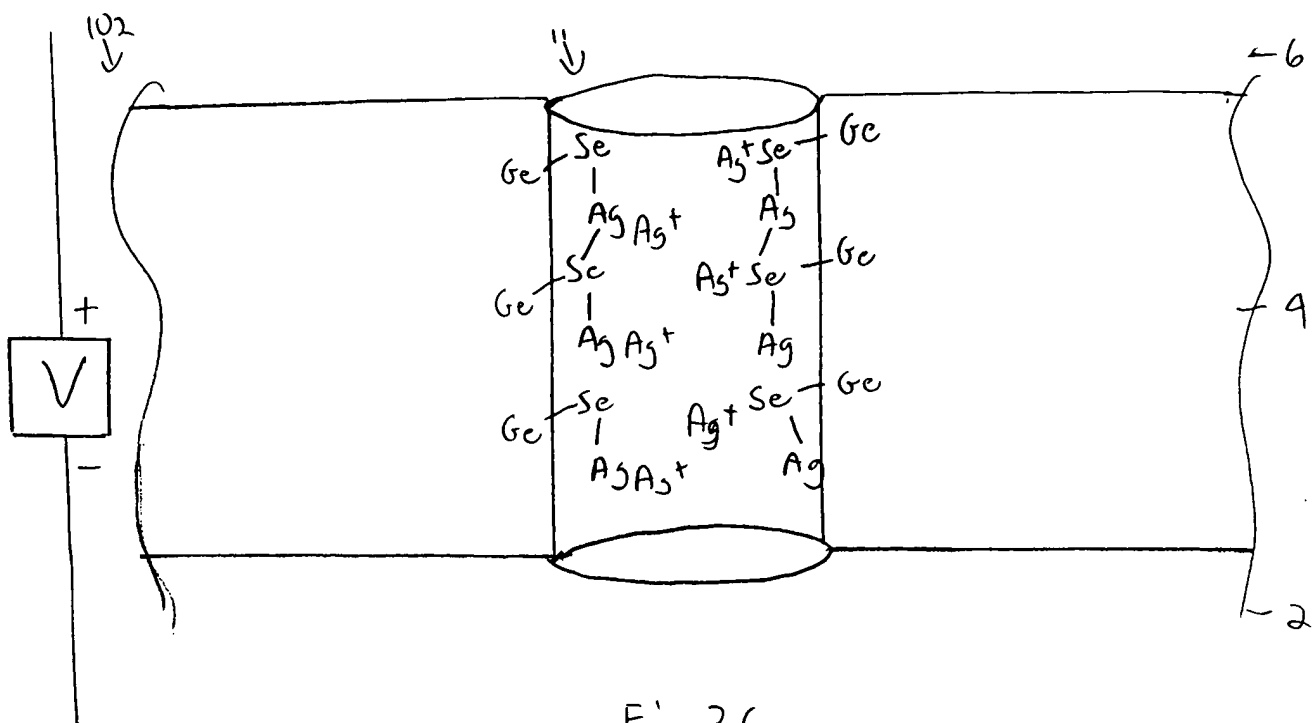


Fig. 3C

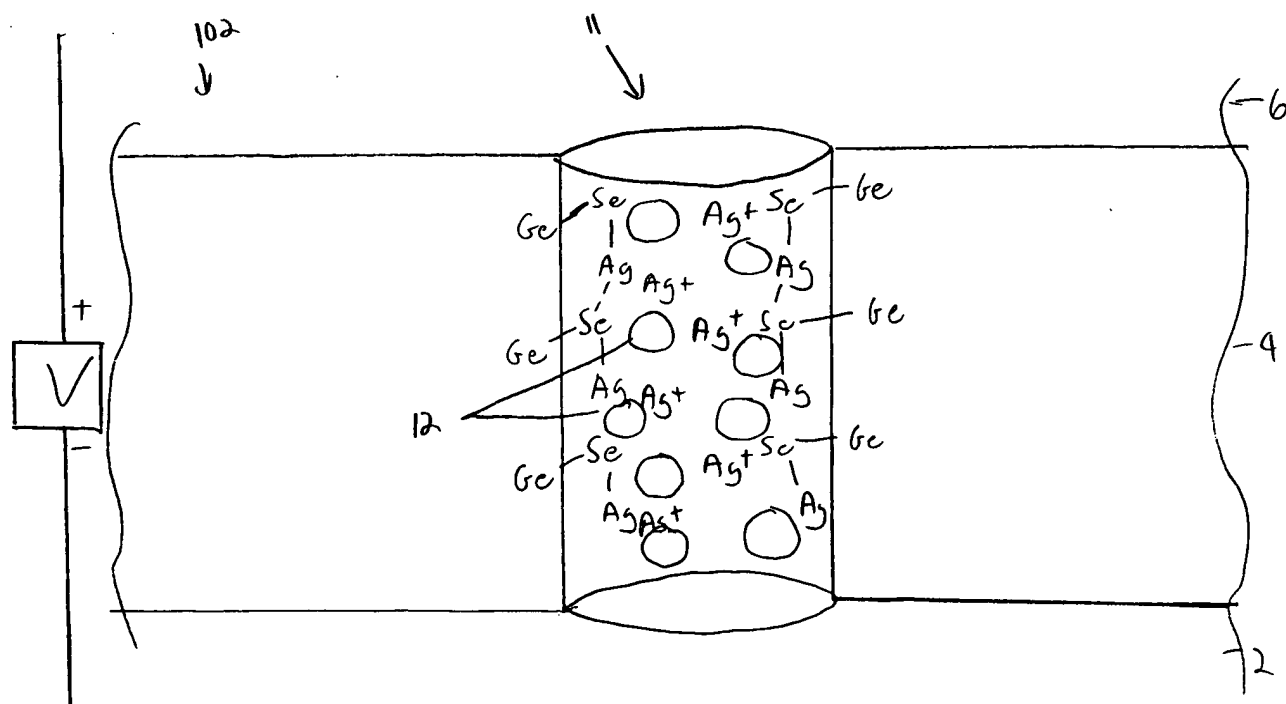


Fig. 3D

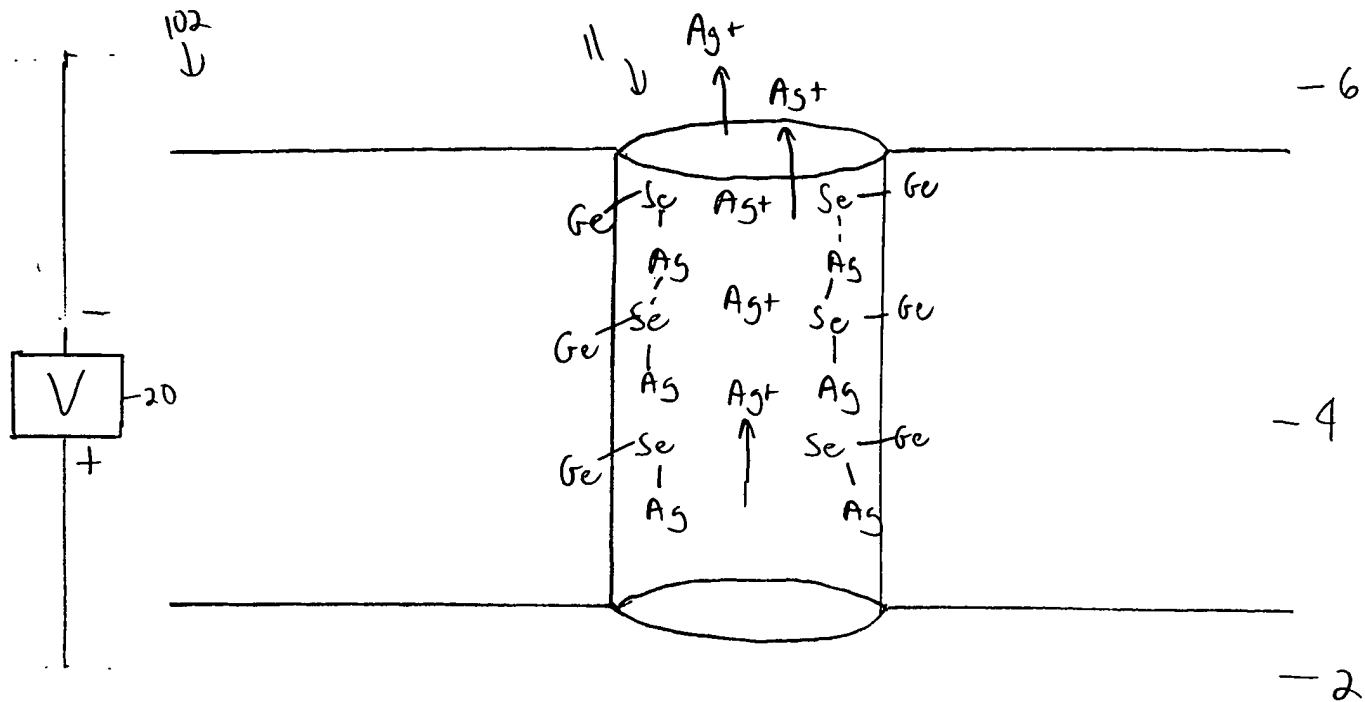


Fig. 3E

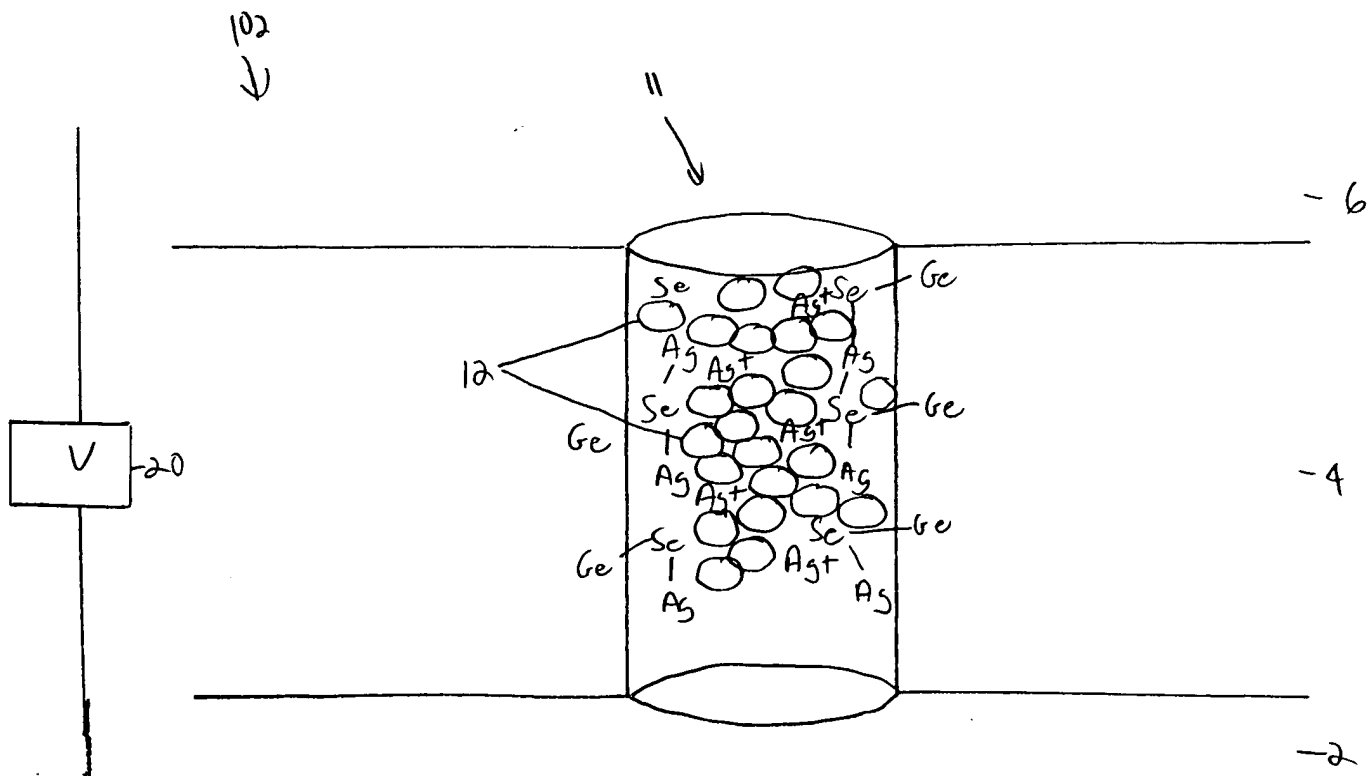


Fig. 3F

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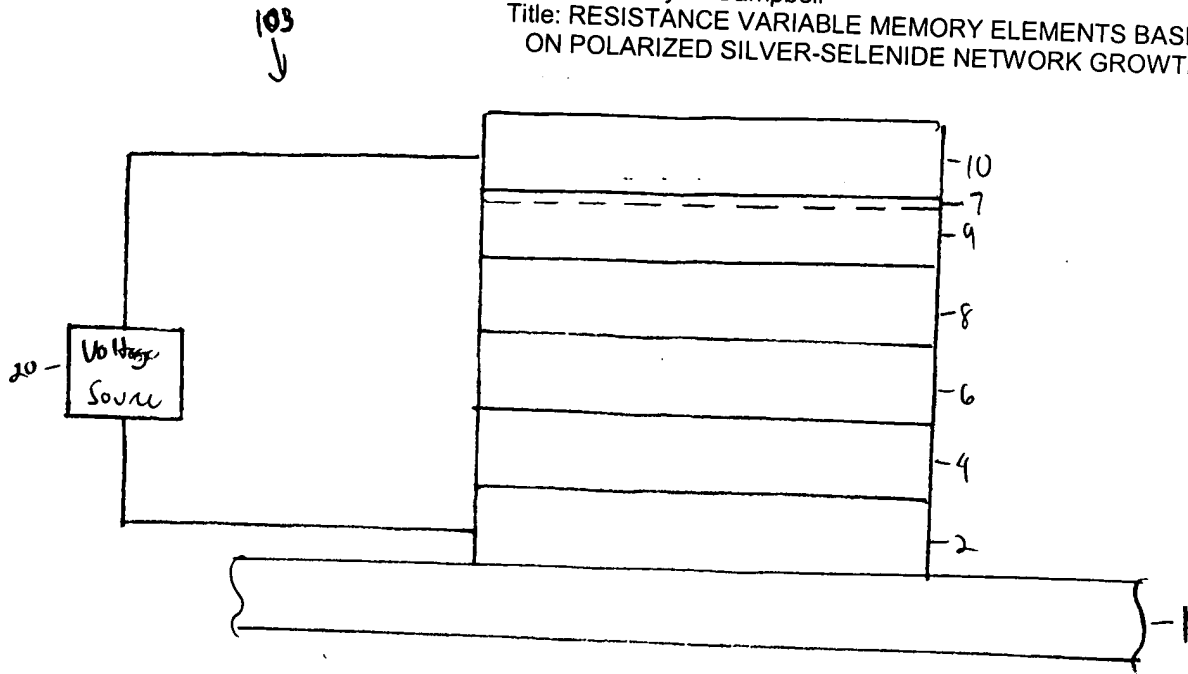


Fig. 4A

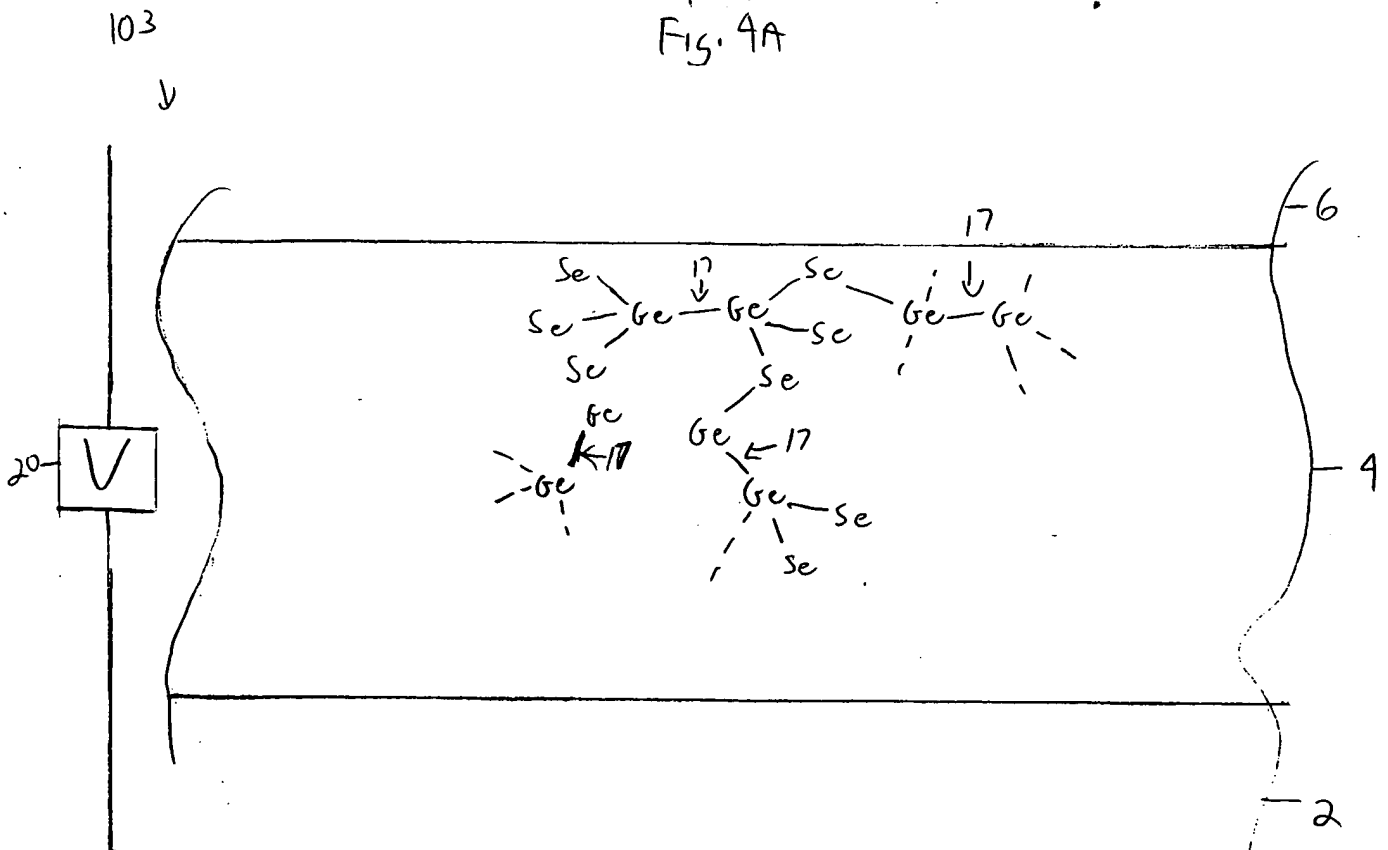


Fig. 4B

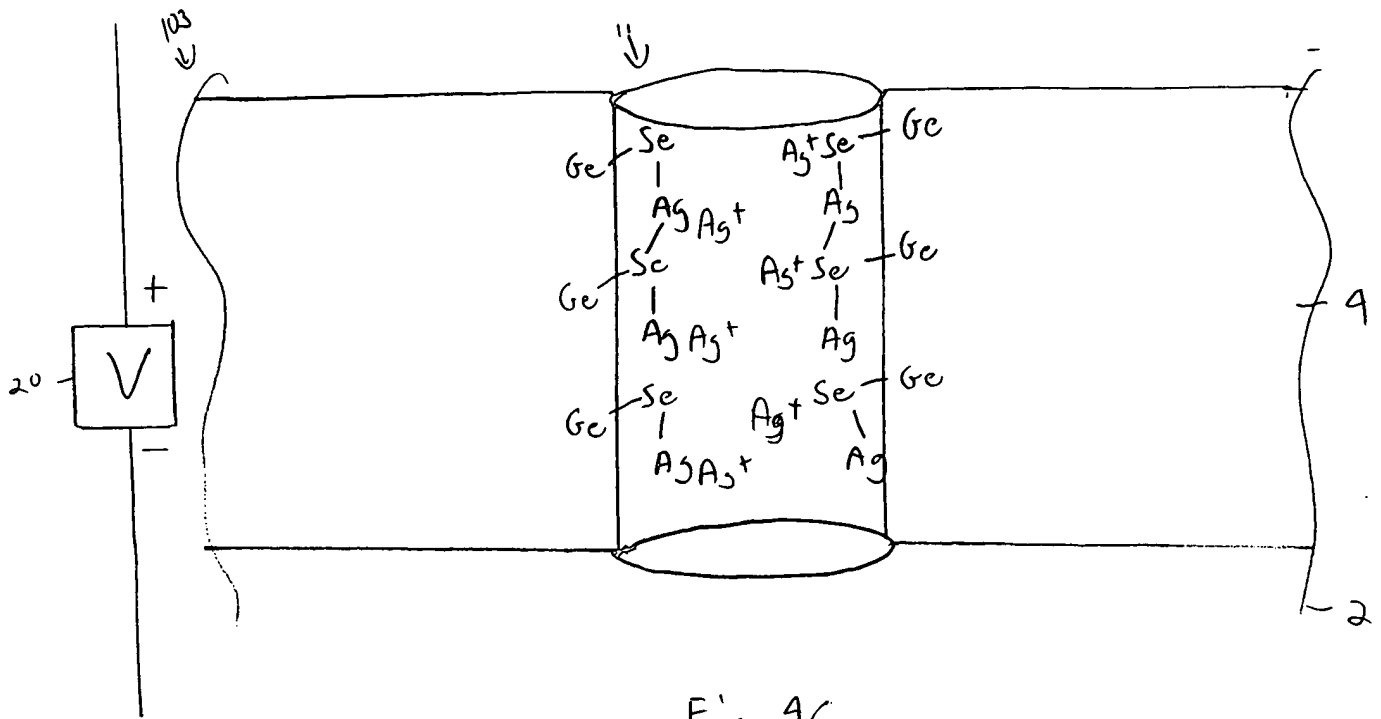


Fig. 4C

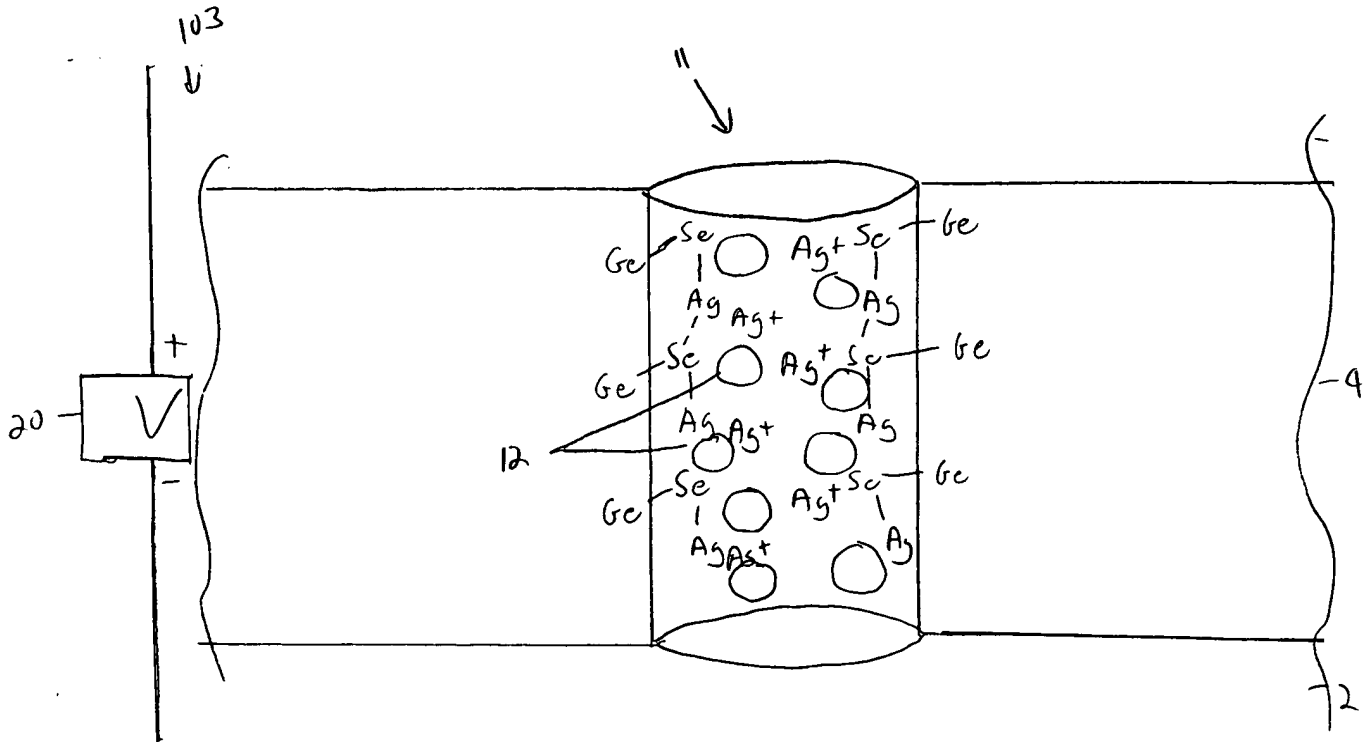


Fig. 4D

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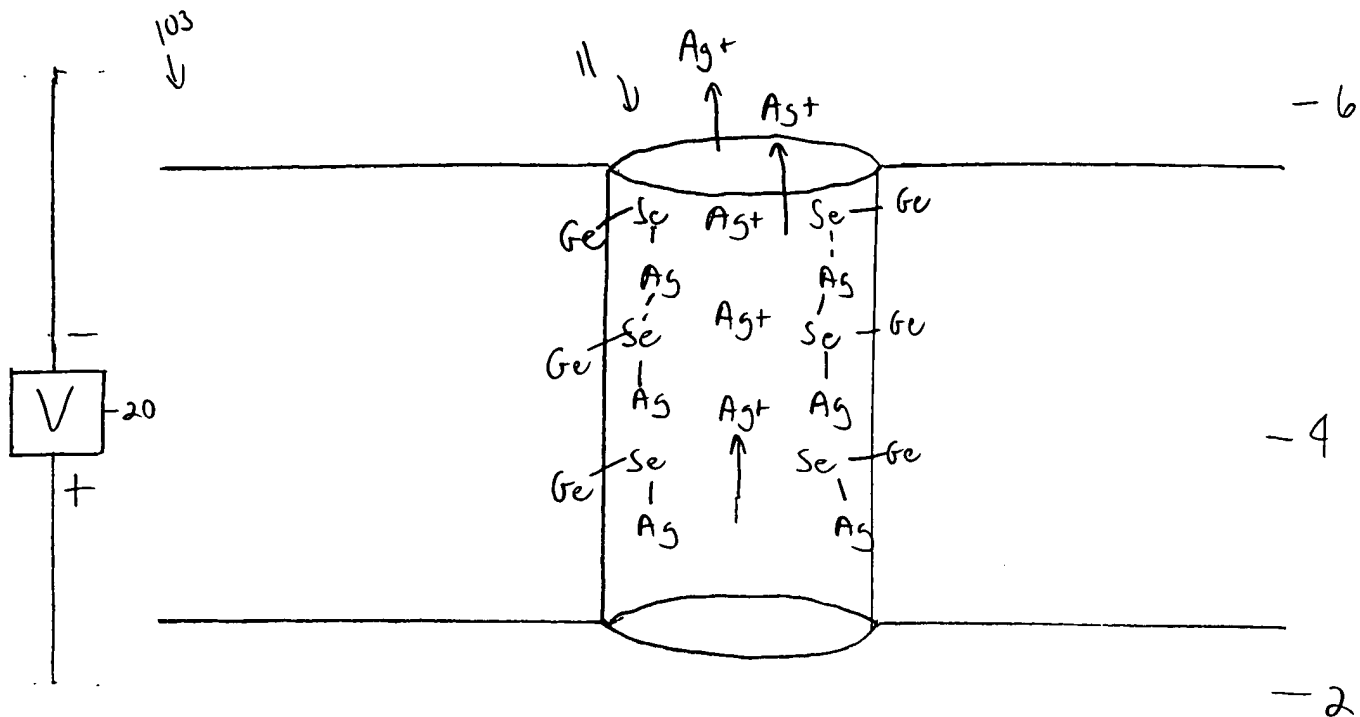


Fig. 4E

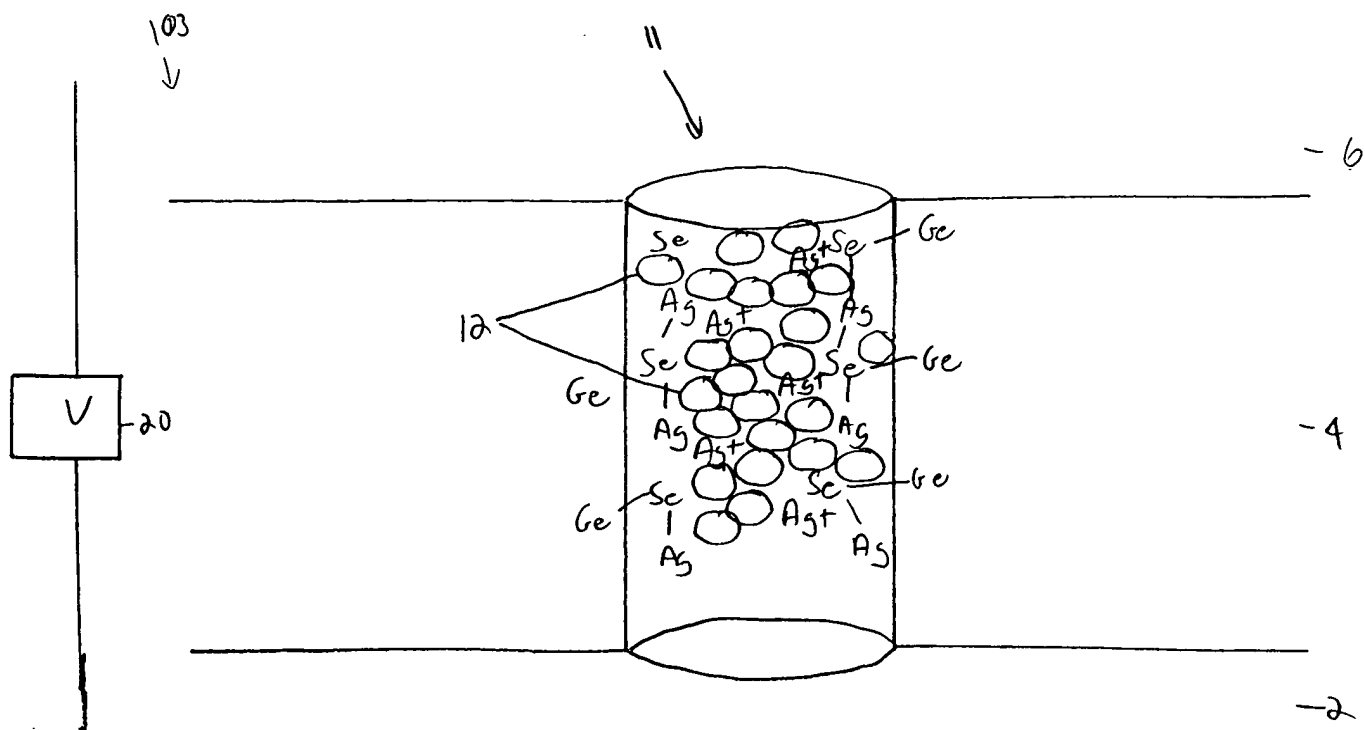


Fig. 4F

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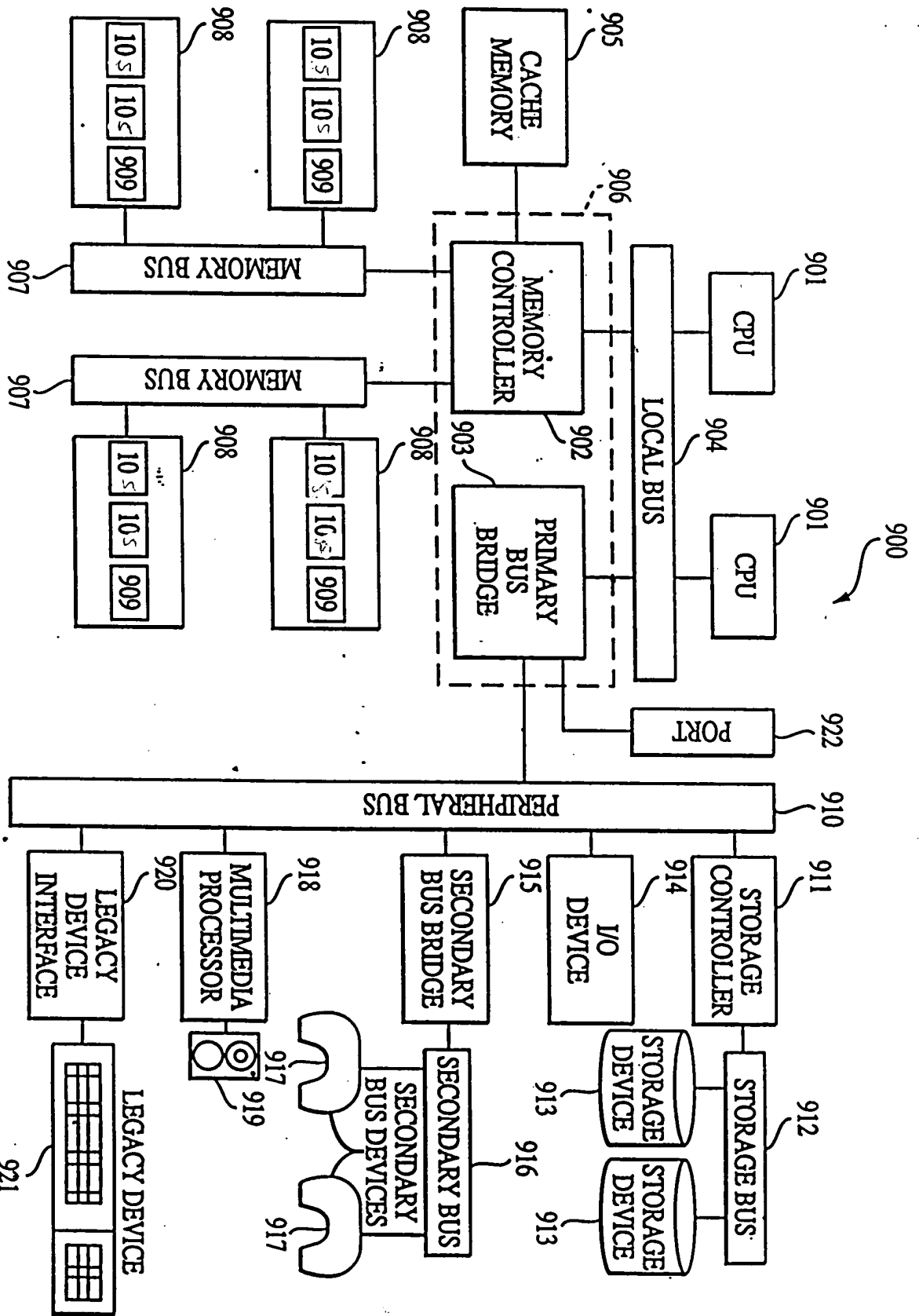


FIG. 5

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